

UNISONIC TECHNOLOGIES CO., LTD

## UTT30P06

Preliminary

# 60V, 30A P-CHANNEL POWER MOSFET

### DESCRIPTION

The UTC **UTT30P06** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance. It can also withstand high energy in the avalanche.

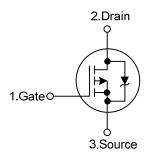
The UTC **UTT30P06** is suitable for low voltage and high speed switching applications

#### FEATURES

\*  $R_{DS(ON)}$ =0.067 $\Omega$  @  $V_{GS}$ =-10V,  $I_D$ =-15A

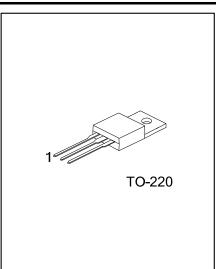
\* High Switching Speed

#### SYMBOL



#### ORDERING INFORMATION

Ordering	Package	Pin Assignment			Deaking		
Lead Free	Lead Free Halogen Free		1	2	3	Packing	
UTT30P06L-TA3-T	UTT30P06G-TA3-T	TO-220	G	D	S	Tube	
Note: Pin Assignment: G: Gate D: Drain S: Source							
Note: Pin Assignment: G: Gate D: Drain S: Source		(1) T: Tube (2) TA3: TO-220 (3) G: Halogen Fr	ee, L: Le	ad Free	1		



#### ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>c</sub>=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT	
Drain-Source Voltage			V <sub>DSS</sub>	-60	V	
Drain-Gate Voltage (R <sub>GS</sub> =1.0 MΩ)			V <sub>DGR</sub>	-60	V	
Gate-Source Voltage	Continuous		V <sub>GSS</sub>	±15	V	
	Non-repetitiv	ve (t <sub>p</sub> ≤10ms)	V <sub>GSM</sub>	±25	V	
Drain Current	Continuous	T <sub>C</sub> =25°C	I <sub>D</sub>	-30	А	
	Continuous	T <sub>C</sub> =100°C	I <sub>D</sub>	-19	А	
	Pulsed (t <sub>p</sub> ≤10	)µs)	I <sub>DM</sub>	-105	А	
Power Dissipation			D	125	W	
Derate Above 25°C			P <sub>D</sub>	0.83	W/°C	
Junction Temperature			TJ	+175	°C	
Storage Temperature			T <sub>STG</sub>	-55~+175	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. When surface mounted to an FR4 board using the minimum recommended pad size.

#### THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	62.5	°C/W
Junction to Case	θ <sub>JC</sub>	1.2	°C/W



#### ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	I <sub>D</sub> =-0.25mA, V <sub>GS</sub> =0V	-60			V
Drain-Source Leakage Current		I <sub>DSS</sub>	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-10	μA
Gate- Source Leakage	Forward		V <sub>GS</sub> =+15V, V <sub>DS</sub> =0V			+100	nA
Current	Reverse	I <sub>GSS</sub>	V <sub>GS</sub> =-15V, V <sub>DS</sub> =0V			-100	nA
<b>ON CHARACTERISTICS</b> (No	te 1)						
Gate Threshold Voltage		V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250µA	-2.0	-2.6	-4.0	V
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A		0.067	0.08	Ω
Durain Courses On Maltana		V	V <sub>GS</sub> =-10V, I <sub>D</sub> =-30A		-2.0	-2.9	V
Drain-Source On-Voltage		V <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A, T <sub>J</sub> =150°C			-2.8	V
DYNAMIC PARAMETERS							
Input Capacitance		CISS			1562	2190	pF
Output Capacitance		C <sub>OSS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-25V, f=1.0MHz		524	730	pF
Reverse Transfer Capacitance		C <sub>RSS</sub>			154	310	pF
SWITCHING PARAMETERS	(Note 2)						
Gate Charge		QT			54	80	nC
		Q <sub>1</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-48V, I <sub>D</sub> =-30A		9.0		nC
		Q <sub>2</sub>	$V_{GS}$ 10V, $V_{DS}$ 40V, $I_D$ 50A		26		nC
		Q <sub>3</sub>			20		nC
Turn-ON Delay Time		t <sub>D(ON)</sub>			14.7	30	ns
Rise Time		t <sub>R</sub>	V <sub>GS</sub> =-10V, V <sub>DD</sub> =-30V,		25.9	50	ns
Turn-OFF Delay Time		t <sub>D(OFF)</sub>	I <sub>D</sub> =-30A, R <sub>G</sub> =9.1Ω		98	200	ns
Fall-Time		t <sub>F</sub>			52.4	100	ns
SOURCE- DRAIN DIODE RA	TINGS AND	CHARACT	ERISTICS				
Drain-Source Diode Forward	/oltage	V <sub>SD</sub>	I <sub>S</sub> =-30A, V <sub>GS</sub> =0V		-2.3	-3.0	V
Body Diode Reverse Recovery Time		t <sub>RR</sub>	I <sub>S</sub> =-30A, V <sub>GS</sub> =0V,		175		ns
Body Diode Reverse Recovery Charge		Q <sub>RR</sub>	dl <sub>s</sub> /dt=-100A/µs		0.965		μC

Notes: 1. Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%.

2. Switching characteristics are independent of operating junction temperature.

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